

Insulated Gate Bi-Polar Transistor Type T0800EB45G

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{CES}	Collector – emitter voltage	4500	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate.	2800	V
V_{GES}	Peak gate – emitter voltage	± 20	V

	RATINGS	MAXIMUM LIMITS	UNITS
$I_{C(DC)}$	DC collector current, IGBT	800	A
I_{CRM}	Repetitive peak collector current, $t_p=1ms$, IGBT	1600	A
$I_{F(DC)}$	Continuous DC forward current, Diode	800	A
I_{FRM}	Repetitive peak forward current, $t_p=1ms$, Diode	1600	A
I_{FSM}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}=60\%V_{RRM}$, Diode (Note 4)	5720	A
I_{FSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}\leq 10V$, Diode (Note 4)	6300	A
P_{MAX}	Maximum power dissipation, IGBT (Note 2)	6.4	kW
$(di/dt)_{cr}$	Critical diode di/dt (note 3)	2000	A/ μs
T_j	Operating temperature range.	-40 to +125	$^{\circ}C$
T_{stg}	Storage temperature range.	-40 to +125	$^{\circ}C$

Notes: -

- 1) Unless otherwise indicated $T_j = 125^{\circ}C$.
- 2) $T_{sink} = 25^{\circ}C$, double side cooled.
- 3) Maximum commutation loop inductance 200nH.
- 4) Half-sinewave, $125^{\circ}C$ T_j initial.

Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V _{CE(sat)}	Collector – emitter saturation voltage	-	2.75	3.2	I _C = 800A, V _{GE} = 15V, T _J = 25°C	V
		-	3.50	3.9	I _C = 800A, V _{GE} = 15V	V
V _{T0}	Threshold voltage	-	-	1.74	Current range: 267 - 800A	V
r _T	Slope resistance	-	-	2.70		mΩ
V _{GE(TH)}	Gate threshold voltage	-	5.2	-	V _{CE} = V _{GE} , I _C = 85mA	V
I _{CES}	Collector – emitter cut-off current	-	20	50	V _{CE} = V _{CES} , V _{GE} = 0V	mA
I _{GES}	Gate leakage current	-	-	±15	V _{GE} = ±20V	μA
C _{ies}	Input capacitance	-	135	-	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	nF
t _{d(on)}	Turn-on delay time	-	1.8	-	I _C = 800A, V _{CE} = 2800V, di/dt = 1700A/μs	μs
t _{r(V)}	Rise time	-	3.3	-		μs
Q _{g(on)}	Turn-on gate charge	-	5	-	V _{GE} = ±15V, L _S = 200nH	μC
E _{on}	Turn-on energy	-	6.3	-	R _{g(ON)} = 5.6Ω, R _{g(OFF)} = 5.6Ω, C _{GE} = 90nF	J
t _{d(off)}	Turn-off delay time	-	3.0	-	Integral diode used as freewheel diode (Note 3 & 4)	μs
t _{f(I)}	Fall time	-	2.4	-		μs
Q _{g(off)}	Turn-off gate charge	-	8	-		μC
E _{off}	Turn-off energy	-	3.7	-		J
I _{SC}	Short circuit current	-	2800	-	V _{GE} = +15V, V _{CC} = 2800V, V _{CEmax} ≤ V _{CES} , t _p ≤ 10μs	A

Diode Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V _F	Forward voltage	-	3.35	3.6	I _F = 800A, T _J = 25°C	V
		-	3.5	3.8	I _F = 800A	V
V _{To}	Threshold voltage	-	-	2.05	Current range 267 - 800A	V
r _T	Slope resistance	-	-	2.19		mΩ
I _{rm}	Peak reverse recovery current	-	800	-	I _F = 800A, V _{GE} = -15V, di/dt = 1700A/μs	A
Q _{rr}	Recovered charge	-	1020	-		μC
t _{rr}	Reverse recovery time, 50% chord	-	1.5	-		μs
E _r	Reverse recovery energy	-	1.2	-		J

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R _{thJK}	Thermal resistance junction to sink, IGBT	-	-	15.6	Double side cooled	K/kW
		-	-	25.4	Collector side cooled	K/kW
		-	-	40.5	Emitter side cooled	K/kW
R _{thJK}	Thermal resistance junction to sink, Diode	-	-	24.7	Double side cooled	K/kW
		-	-	37.9	Cathode side cooled	K/kW
		-	-	70.8	Anode side cooled	K/kW
F	Mounting force	25	-	35	Note 2	kN
W _t	Weight	-	1.2	-		kg

Notes:-

- 1) Unless otherwise indicated T_J = 125°C.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C_{GE} is additional gate – emitter capacitance added to output of gate drive
- 4) Figures 6 to 9 are obtained using integral diode as freewheeling diode

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

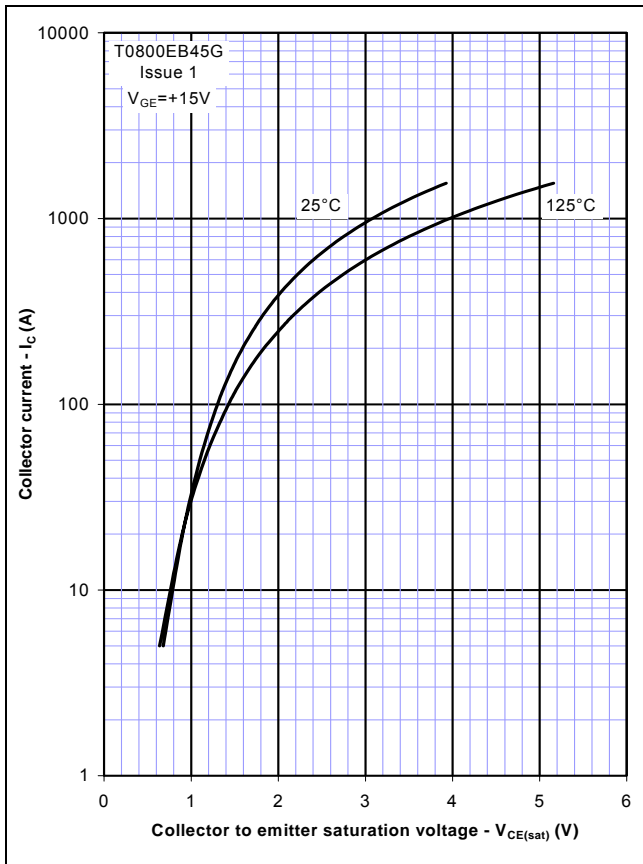


Figure 2 – Typical output characteristic

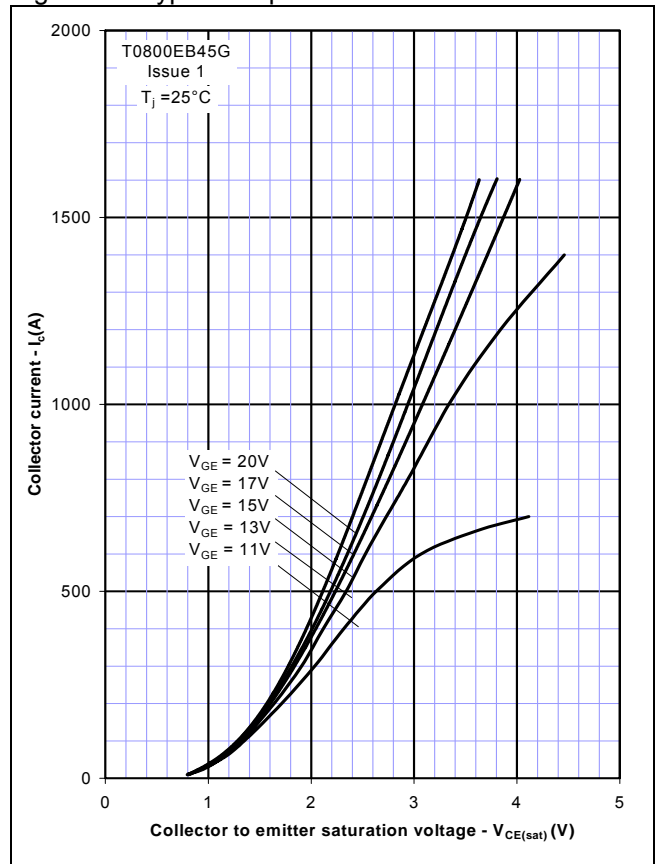


Figure 3 – Typical output characteristic

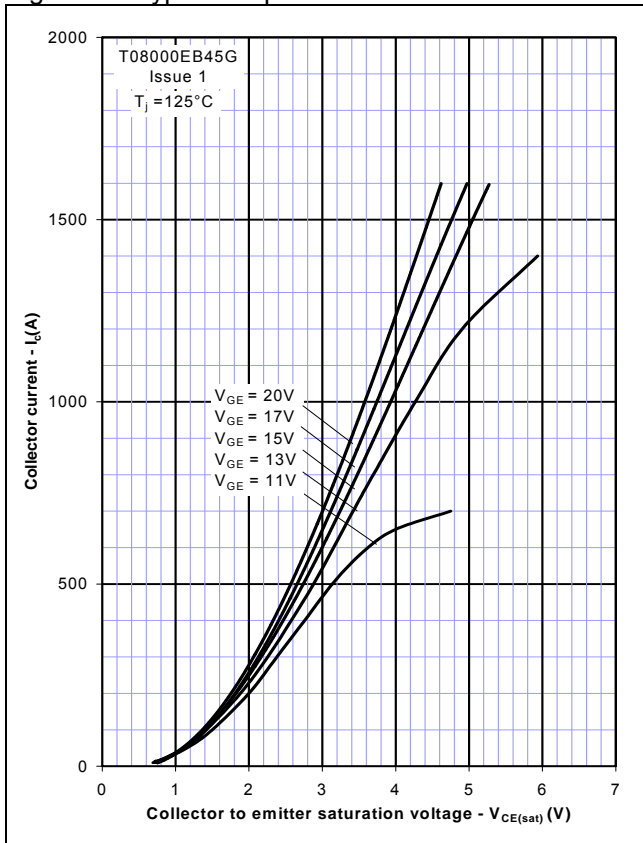


Figure 4 – Typical turn-on delay time vs gate resistance

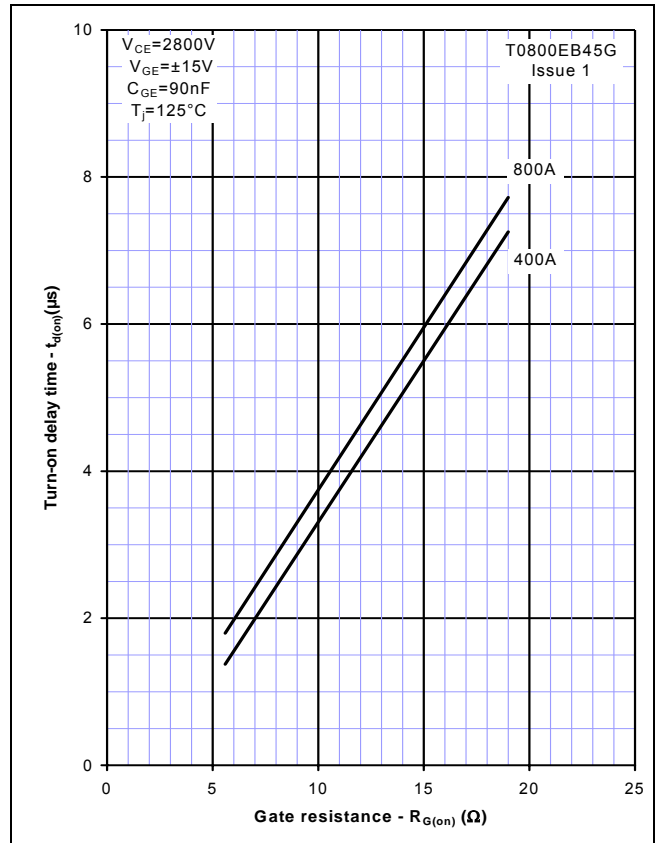


Figure 5 – Typical turn-off delay time vs. gate resistance

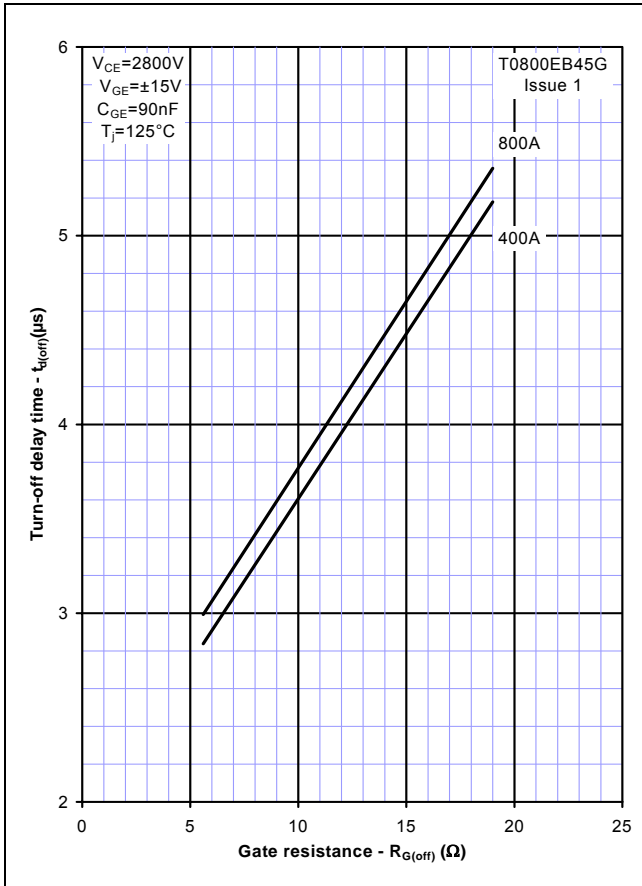


Figure 6 – Typical turn-on energy vs. collector current

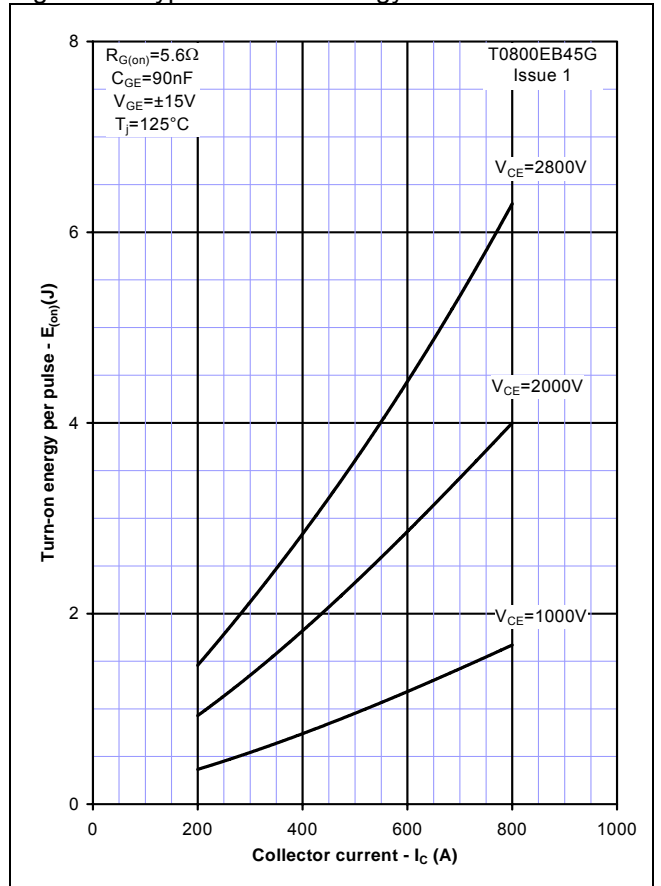


Figure 7 – Typical turn-on energy vs. di/dt

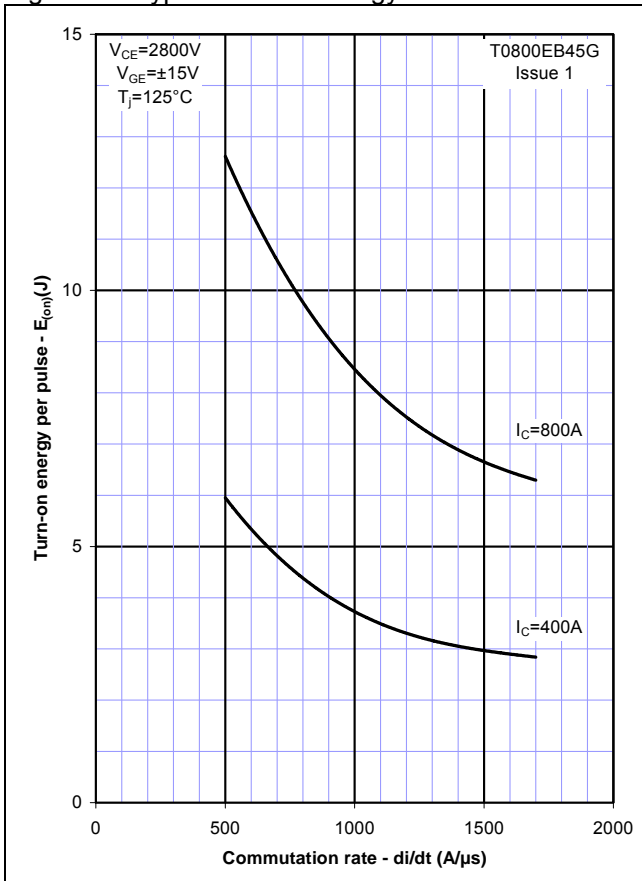


Figure 8 – Typical turn-off energy vs. collector current

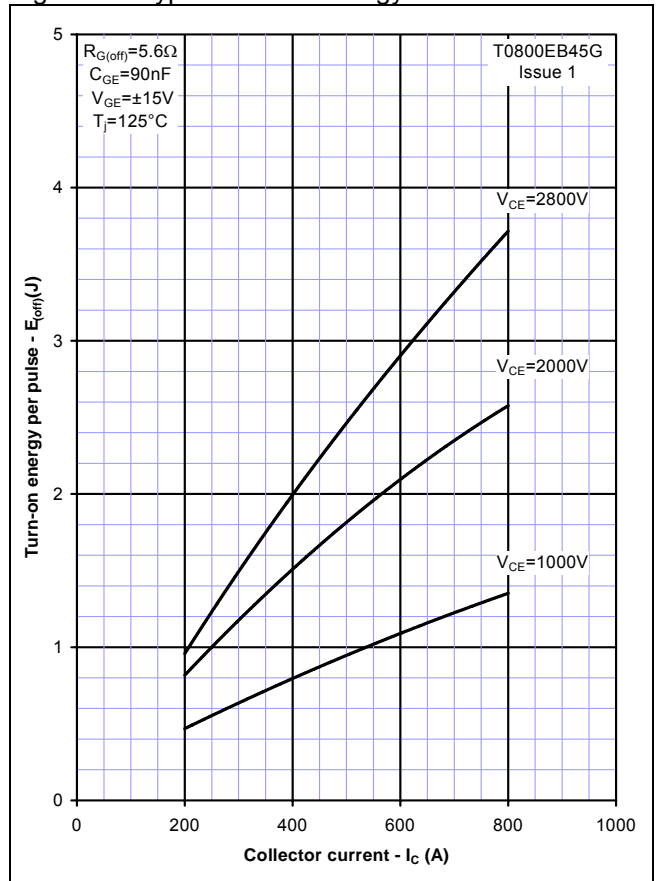


Figure 9 – Turn-off energy vs voltage

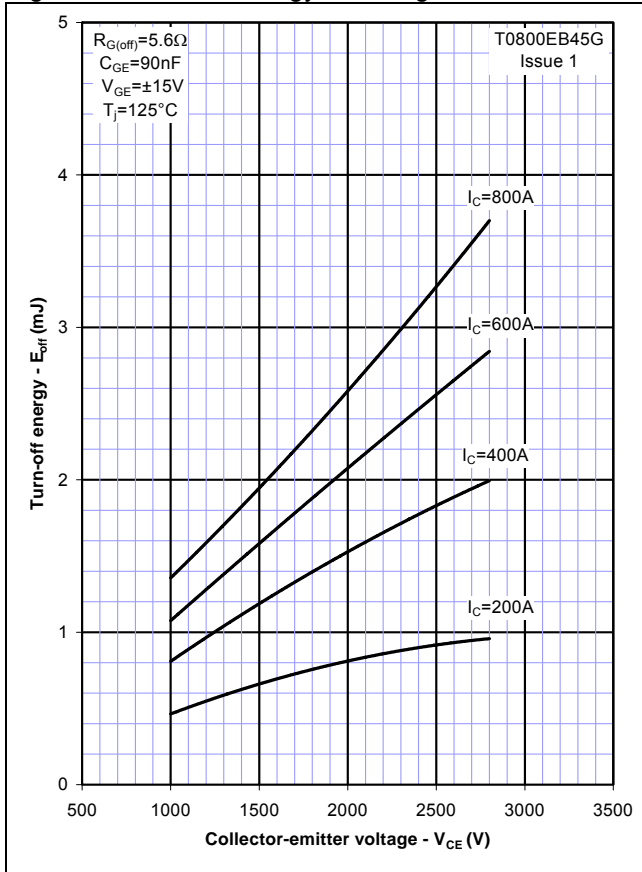


Figure 10 – Safe operating area

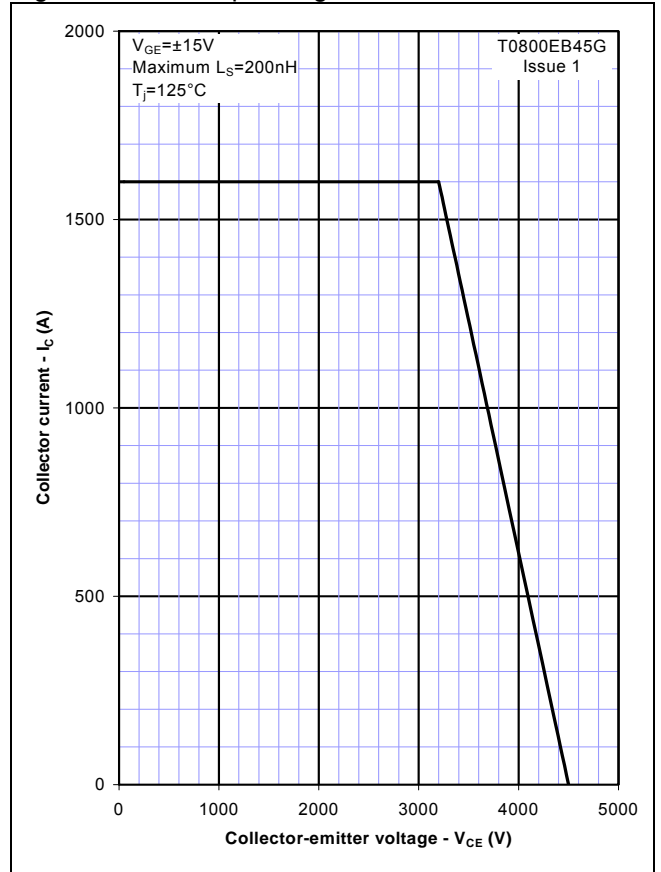


Figure 11 – Typical diode forward characteristics

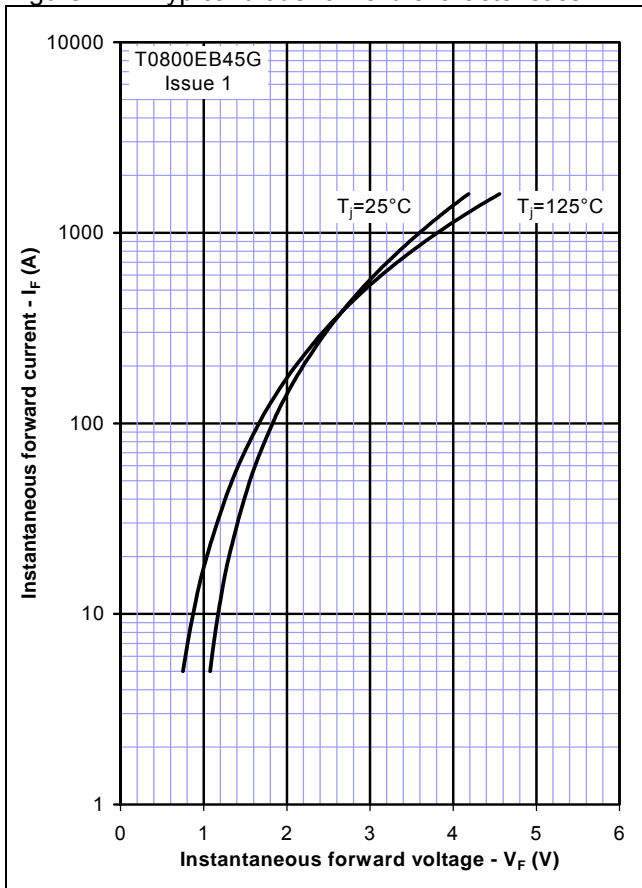


Figure 12 – Typical recovered charge

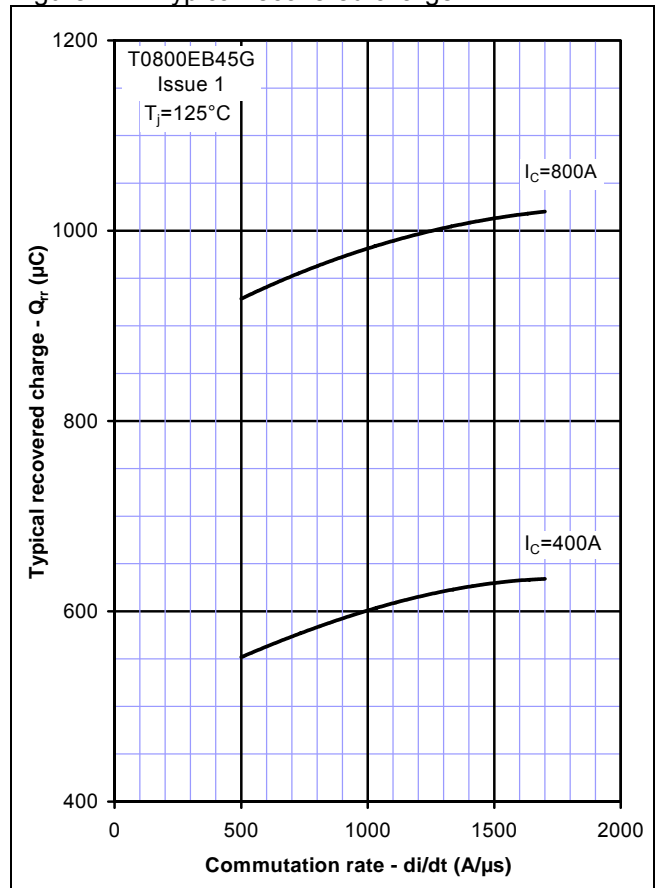


Figure 13 – Typical reverse recovery current

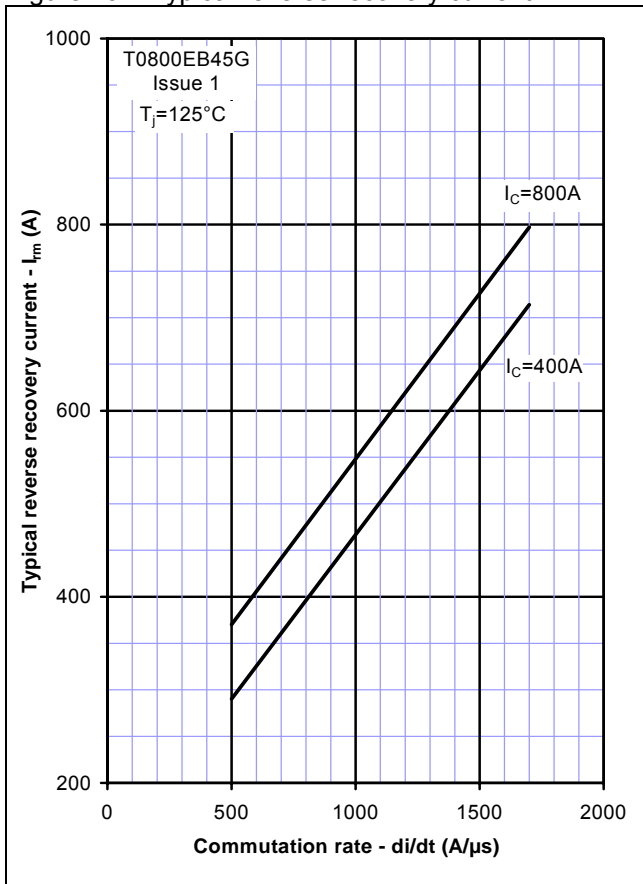


Figure 14 – Typical reverse recovery time

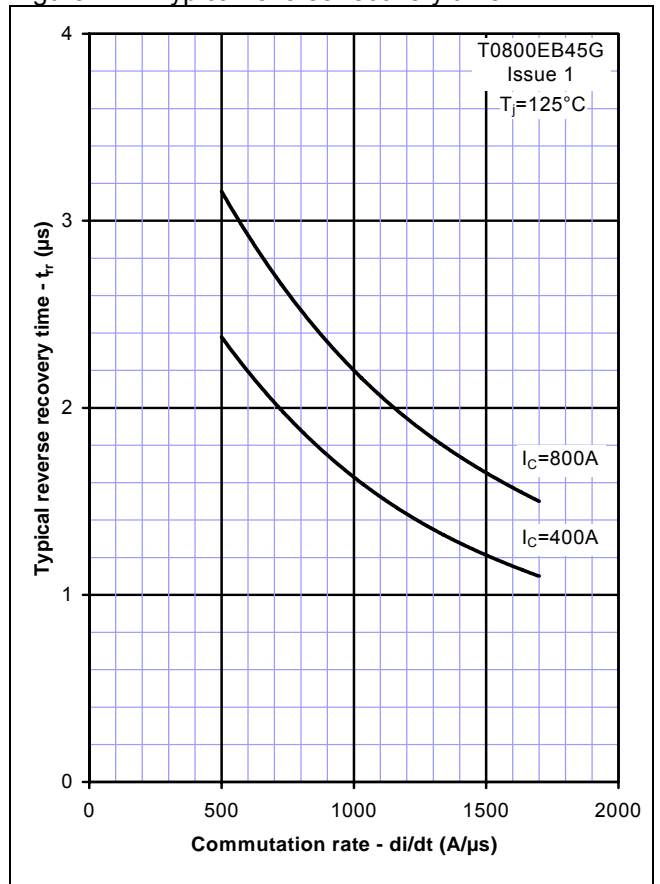


Figure 15 – Transient thermal impedance (IGBT)

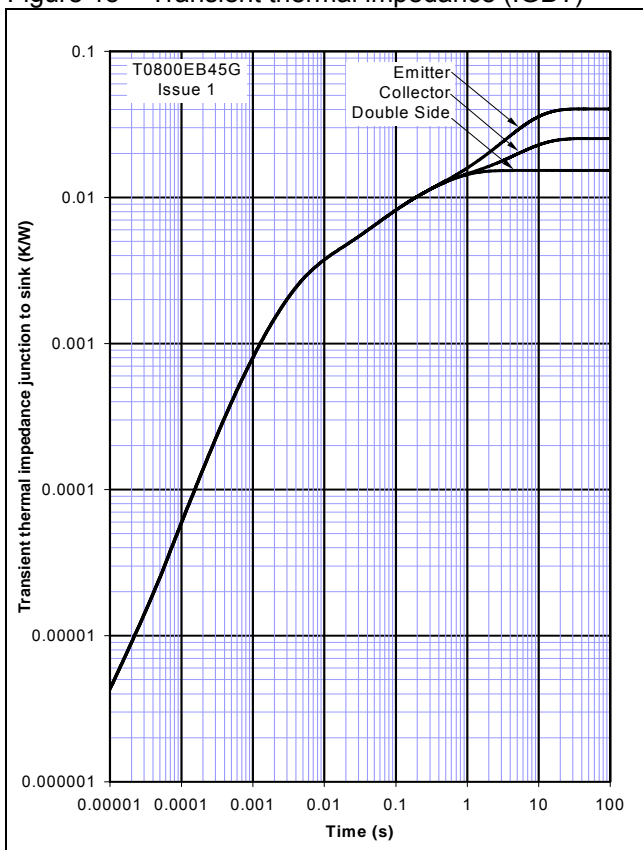
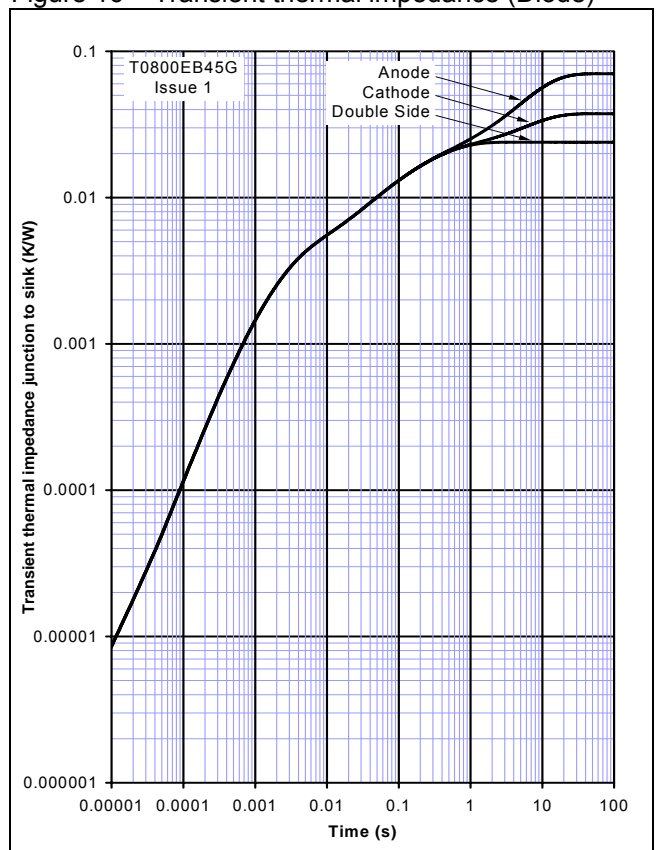
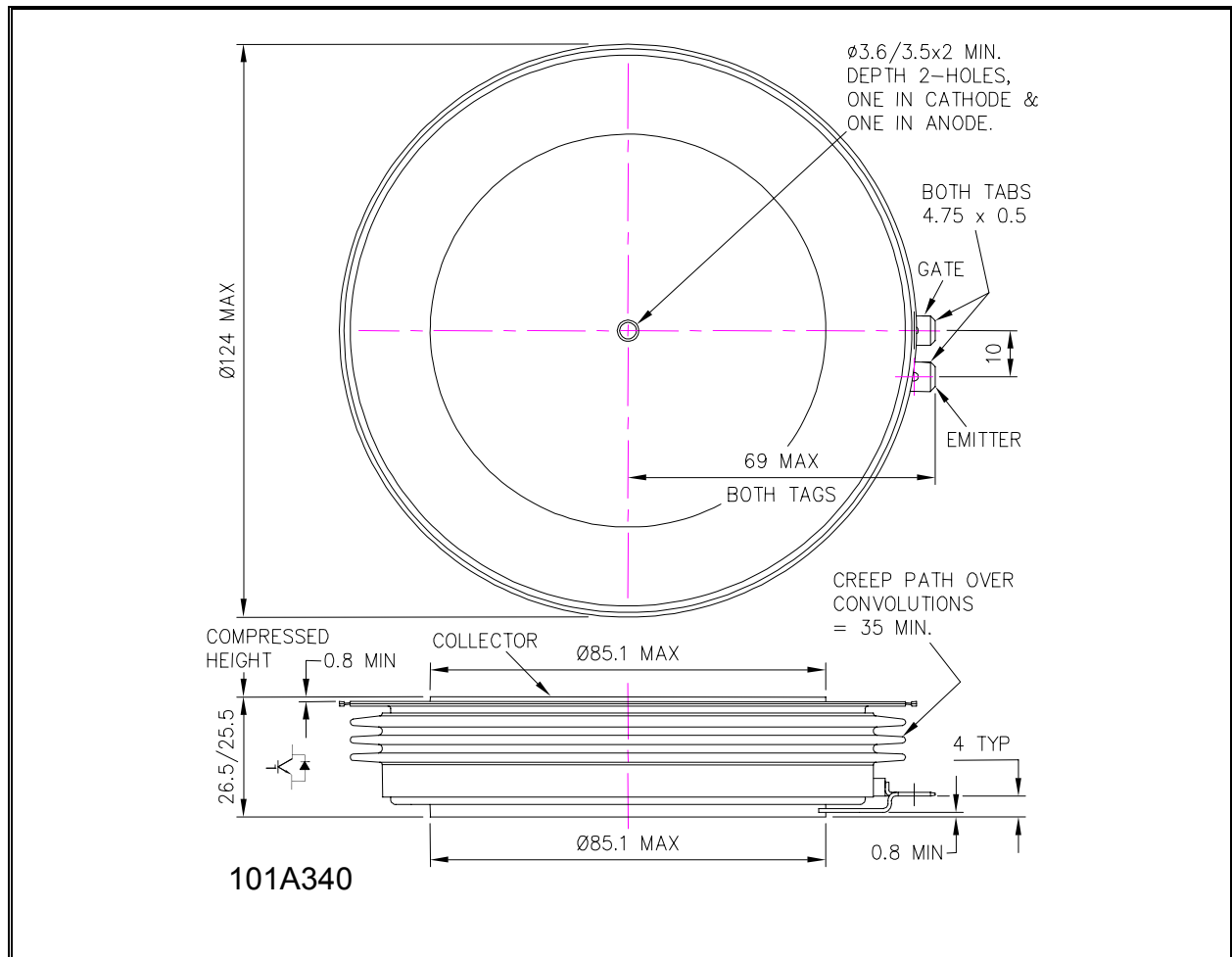


Figure 16 – Transient thermal impedance (Diode)



Outline Drawing & Ordering Information



ORDERING INFORMATION			
(Please quote 10 digit code as below)			
T0800	EB	45	G
Fixed type Code	Fixed Outline Code	Voltage Grade $V_{CES}/100$ 45	Fixed format code

Typical order code: T0800EB45G ($V_{CES} = 4500V$)

IXYS Semiconductor GmbH
 Edisonstraße 15
 D-68623 Lampertheim
 Tel: +49 6206 503-0
 Fax: +49 6206 503-627
 E-mail: marcom@ixys.de

WESTCODE
 An IXYS Company

Westcode Semiconductors Ltd
 Langley Park Way, Langley Park,
 Chippenham, Wiltshire, SN15 1GE.
 Tel: +44 (0)1249 444524
 Fax: +44 (0)1249 659448
 E-mail: WSL.sales@westcode.com

IXYS Corporation
 1590 Buckeye Drive
 Milpitas CA 95035-7418
 Tel: +1 (408) 457 9000
 Fax: +1 (408) 496 0670
 E-mail: sales@ixys.net

www.westcode.com

www.ixys.net

IXYS Long Beach
 IXYS Long Beach, Inc
 2500 Mira Mar Ave, Long Beach
 CA 90815
 Tel: +1 (562) 296 6584
 Fax: +1 (562) 296 6585
 E-mail: service@ixyslongbeach.com

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